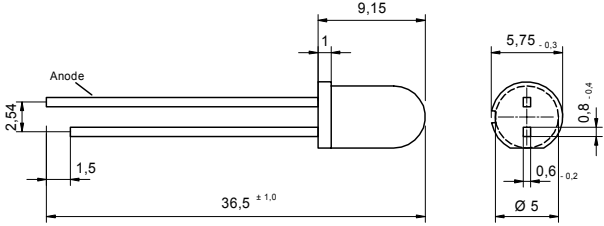


Radiation	Type	Technology	Case
Infrared	DDH	AlGaAs/AlGaAs	5 mm plastic lens

	Description
	<p>High-power, high-speed infrared LED in standard 5 mm package (T1), housing without standoff leads</p> <p>Note: Special packages with standoff available on request</p>
	Applications
	Optical communications, safety equipment, automation, optical sensors

Maximum Ratings

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Forward current (DC)		I_F	100	mA
Peak forward current	$(t_p \leq 50 \mu\text{s}, t_p/T = 1/2)$	I_{FM}	200	mA
Operating temperature range		T_{amb}	-20 to +80	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-30 to +100	$^{\circ}\text{C}$
Junction temperature		T_J	100	$^{\circ}\text{C}$

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage*	$I_F = 20 \text{ mA}$	V_F		1.6	1.9	V
Reverse voltage	$I_R = 100 \mu\text{A}$	V_F	5			V
Radiant power*	$I_F = 20 \text{ mA}$	Φ_e	4.5	6.5		mW
Radiant power*	$I_F = 100 \text{ mA}$	Φ_e		33		mW
Radiant intensity*	$I_F = 100 \text{ mA}$	I_e		190		mW/sr
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p	830	840	850	nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		35		nm
Viewing angle	$I_F = 20 \text{ mA}$	φ		20		deg.
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		40		ns

*measured after 30s current flow

Note: All measurements carried out on *EPIGAP* equipment

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.

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